Call for Paper

5th International WorkShop on New Group IV Semiconductor Nanoelectronics

Jan. 29(Fri.) - 30(Sat.), 2010

http://www.murota.riec.tohoku.ac.jp/SiGeC2010/

Laboratory for Nanoelectronics and Spintronics
Research Institute of Electrical Communication
Tohoku University, SENDAI, JAPAN

International Symposium on Research Institute of Electrical Communication, Tohoku University

The 5th International Workshop on New Group IV Semiconductor Nanoelectronics will be held in Laboratory for Nanoelectronics and Spintronics, Research Institute of Electrical Communication, Tohoku University, Sendai, Japan, on January 29-30, 2010. This workshop will focus on new group IV semiconductor nanoelectronics.

SCOPE

· Theoretical and Experimental Aspects on Homo-and Heteroepitaxial Growth
· Growth Mechanisms of Molecular Beam Epitaxy and Chemical Vapor Deposition
· Formation and Properties of Self-Organized/Quantum-Confined Structures
· Novel Growth Techniques
· Electronic and Crystallographic Structures of Surfaces and Interfaces
· Si-Ge and Si-Ge-C and Other Group IV Materials
· Silicides/Si(Ge, C) Heterostructures
· Oxides and Nitrides/Si(Ge, C) Heterostructures
· Electronic Device Applications of Si/Ge(C) Systems
· Optical Device Applications of Si/Ge(C) Systems
· Si-Based Light Emission and Detection
· Relaxed Buffers, Compliant Substrates
· Doping in Group IV Systems
· Device Technology for Si-Based Group IV Systems

SUBMISSION OF ABSTRACTS


PDF or MS Word file of Camera-ready two-page abstract (one-page main text and one-page figures), written in English on white bond paper (A4 size; 2.5cm margin on four sides), should be submitted to the Program Chairman at the CORRESPONDENCE address.

The abstract is recommended to be printed in Black/White. (Abstracts will be published in Black/White.)

The abstract should be headed by the title, author(s), affiliation(s), address, telephone number, fax number and e-mail address, and clearly describe the originality and new contributions of the work. The title, author(s), affiliation(s), address, telephone number, fax number and e-mail address should also be sent by E-mail to

SiGeNano@riec.tohoku.ac.jp

Papers to be presented at the workshop will be selected by the Program Committee based on the submitted abstracts. The notice of acceptance will be e-mailed to the first author or corresponding author by Dec. 29, 2009.

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REGISTRATION

The registration desk will be open tentatively for 10:30 - 17:00 on Friday, Jan. 29, 2010, 09:00 - 17:00 on Saturday, Jan. 30, 2010.

Your completed registration form should be sent to Prof. J. Murota for advanced registration. A banquet will be held 18:30-20:00 on Friday, January 29, 2010.

Accepted credit cards are VISA and MasterCard. Personal checks and bank checks are NOT ACCEPTABLE.

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<th>Registration Fee</th>
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<td>Banquet Fee</td>
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CORRESPONDENCE

Prof. Junichi Murota
Program Committee Chairman
Research Institute of Electrical Communication,
Tohoku University
2-1-1, Katahira, Aoba-ku, Sendai, 980-8577, Japan
Tel: +81-22-217-5548, Fax: +81-22-217-5551
E-mail: SiGeNano@riec.tohoku.ac.jp